In view of the above amendments and Applicant's comments stated herein, Applicant respectfully requests an early and favorable action on the merits.

Respectfully submitted,

Stanley P. Fisher

Registration Number 24,344

JUAN CARLOS A. MARQUEZ Registration No. 34,072

REED SMITH HAZEL & THOMAS LLP

3110 Fairview Park Drive Suite 1400 Falls Church, Virginia 22042 (703) 641-4200

October 15, 2001

Marked Up Version of the Claims

- 5. A level conversion circuit according to Claims 1 or 4, wherein a high resistance element for pull-up use and a high resistance element for pull-down use are connected respectively in parallel to said first p-channel type MOS transistor and said second n-channel type MOS transistor.
- 6. A level conversion circuit according to Claims 1 set 5; wherein the ratio between the gate width and the gate length of said first p-channel type MOS transistor is set to be greater than the ratio between the gate width and the gate length of said second p-channel type MOS transistor, and the ratio between the gate width and the gate length of said second n-channel type MOS transistor is set to be greater than the ratio between the gate width and the gate length of said first n-channel type MOS transistor.